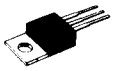
2SB511



2010A

PNP/NPN Triple Diffused Plana
Silicon Transistor

2SD325

Low Frequency Power Amp Applications

©398F

. 5 Watts AF Power amplifier output use. There are complementary pair.

( ):2SB511

Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V_{CBO}		(-)35	V
Collector to Emitter Voltage	V_{CEO}		(-)35	V
Emitter to Base Voltage	V_{EBO}		(-)5	V
Collector Current	I_C		(-)1.5	V
Peak Collector Current	i_{cp}		(-)3	A
Collector Dissipation	P_C		1.75	W
		Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

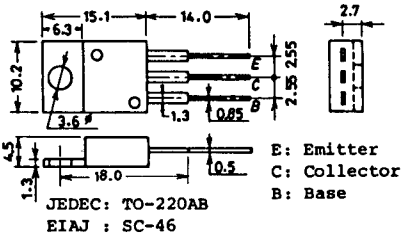
Electrical Characteristics at Ta=25°C

			min	typ	max
Collector Cutoff Current	I_{CBO}	V_{CB}=(-)20V,I_E=0			(-)0.1
Emitter Cutoff Current	I_{EBO}	V_{EB}=(-)4V,I_C=0			(-)1.0
DC Current Gain	$h_{FE}(1)$	V_{CE}=(-)2V,I_C=(-)1A	40*		320*
	$h_{FE}(2)$	V_{CE}=(-)2V,I_C=(-)0.1A	35		
Gain Bandwidth Product	f_T	V_{CE}=(-)5V,I_C=(-)0.5A		8	
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=(-)1.5A,I_B=(-)o.15A			(-)1.0
Base to Emitter Voltage	V_{BE}	I_C=(-)1A,V_{CE}=(-)5V			(-)1.5

*: The 2SB511/2SD325 are classified by 1A h_{FE} as follows:

40	C	80	60	D	120	100	E	200	160	F	320

Case Outline 2010A
(unit:mm)



For details, refer to the description of the 2SD325.